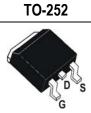
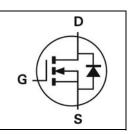


40V N-Channel Power MOSFET

 V_{DSS} , 40V $R_{DS(ON)}$, $3.0m\Omega$ (max.) @ $V_{GS}\text{=}10V$ I_D , 100A $^{Note~3}$





Description	Features
The SG40N01D uses advanced Trench technology and designs to provide excellent R _{DS(ON)} with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	 Lithium-Ion Secondary Batteries Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG40N01D	Halogen-Free	TO-252	D	Tape & Reel	2,500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Paramet	er	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	±20	V
Dunin Course & Courtinous Note 1	T _C =25°C		100 Note 3	А
Drain Current-Continuous Note 1	T _C =100°C	I _D	92.4	А
Drain Current-Pulsed Note 1	·	Ірм	400	А
Desir Courset Continues	T _A =25°C		23.1	А
Drain Current-Continuous	T _A =70°C	I _D	18.5	А
Avalanche Current	·	las	63.5	А
Avalanche Energy, L=0.1mH		Eas	201	mJ
	T _C =25°C		80.6	W
Mayirayra Dayyar Dissination	T _C =100°C		32.3	W
Maximum Power Dissipation	T _A =25°C	P _D	2	W
	T _A =70°C		1.3	W
Storage Temperature Range	<u> </u>	T _{STG}	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	RθJA	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	·	1	1.55	°C/W

1



40V N-Channel Power MOSFET

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =32V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =20A			3.0	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	4222	-	
Output Capacitance	Coss	V _{DS} =20V, V _{GS} =0V, f=1MHz	-	889	-	pF
Reverse Transfer Capacitance	C _{rss}		-	398	ı	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	21	-	
Rise Time	tr	V _{DS} =20V, I _{DS} =30A, V _{GS} =10V,	-	6	-]
Turn-Off Delay Time	$T_{d(off)}$	R _{GEN} =3Ω	-	98	-	ns
Fall Time	t _f		-	17	-	1
Total Gate Charge at 10V	Qg		-	78	-	
Gate to Source Gate Charge	Q _{gs}	V _{DS} =20V, I _{DS} =30A, V _{GS} =10V	-	22	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	4.7	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _{DS} =30A	-	-	1.3	V
Body Diode Reverse Recovery Time	t _{rr}	1 -20 4 -41/44-400 4 /	-	32	-	ns
Body Diode Reverse Recovery Charge	Qrr	I _F =30A, dl/dt=100A/μs	-	120	-	nC

Notes:

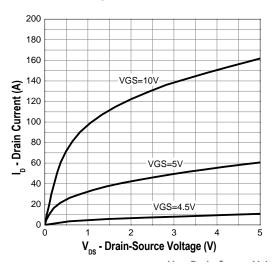
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Reja is guaranteed by design while Reja is determined by the user's board design. Reja shown below for single device operation on FR-4 in still air.
- 3. The maximum current rating is limited by package.



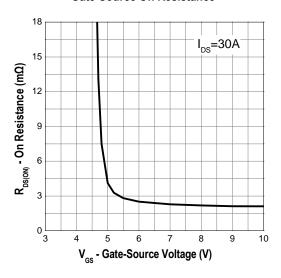
40V N-Channel Power MOSFET

Typical Operating Characteristics

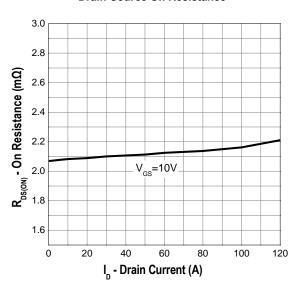
Output Characteristics



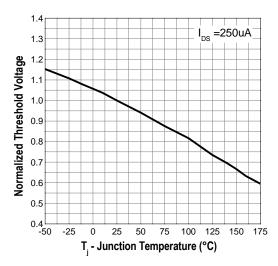
Gate-Source On Resistance



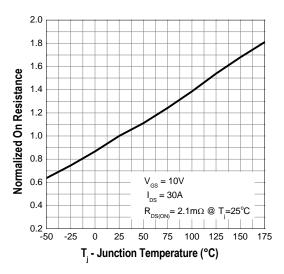
Drain-Source On Resistance



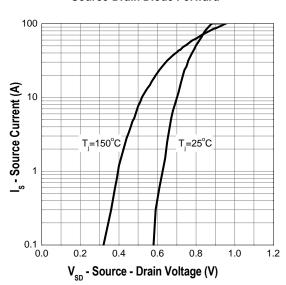
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

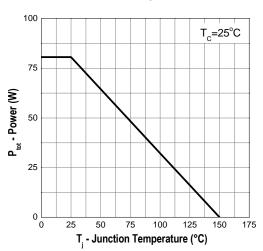




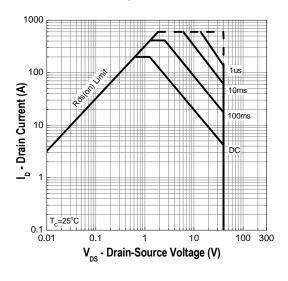
40V N-Channel Power MOSFET

Typical Operating Characteristics (Cont.)

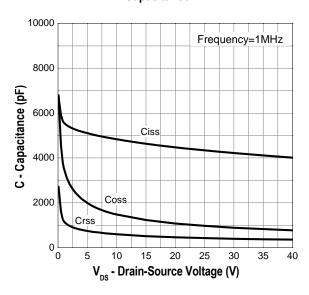
Power Dissipation



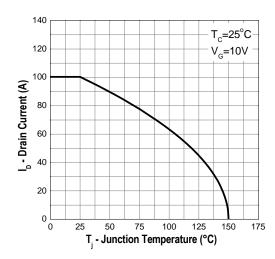
Safe Operation Area



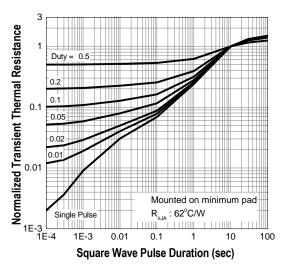
Capacitance



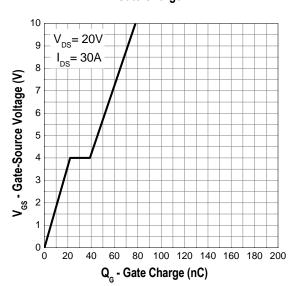
Drain Current



Transient Thermal Impedance



Gate Charge





SG40N01D
40V N-Channel Power MOSFET

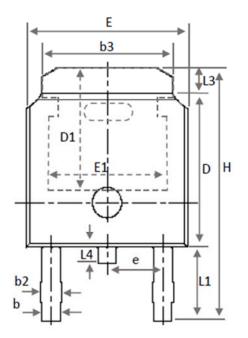
Marking Information

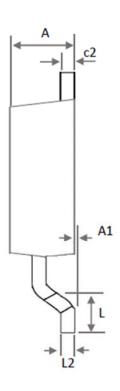
TO-252 (D)	Marking Rule
TO-252 (D) Laser Marking SG40N01D YYMMXXX	Marking Rule Line 1: Device Name SG40N01D Line 2: Date Code YYMMXXX YY: Year Code MM: Month Code XXX: Serial Number
Diagram	



40V N-Channel Power MOSFET

Package of Dimension



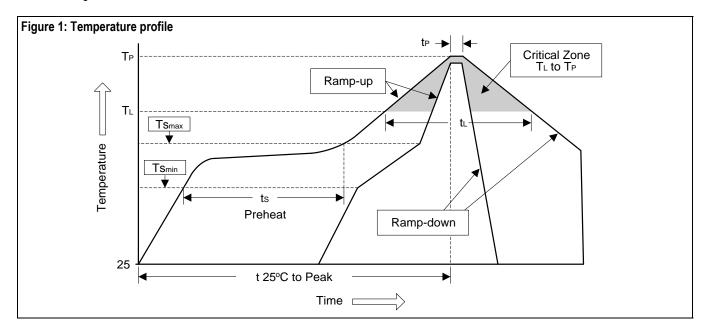


Symbol	Min	Nor	Max
E	6.35	6.54	6.731
L	1.40	1.59	1.78
L1		2.743 Ref	
L2	(0.508 BSC	ĵ.
L3	0.89	1.08	1.27
L4	0.60	0.81	1.01
D	5.97	6.10	6.223
Н	9.40	9.91	10.41
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	4.95	5.21	5.46
е		2.286 BSC	Ĵ
Α	2.18	2.29	2.39
A1	0.00	0.07	0.13
c2	0.46	0.68	0.89
D1	5.21	-	-
E1	4.32	-	8



Soldering Methods for Silicongear's Products1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%

- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 20 ago	20 to 40 and
Temperature (t₂)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



SG40N01D
40V N-Channel Power MOSFET

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